

**Pseudo SRAM**

Part No.	W966D6HBG						
Datasheet							
Description	This is a 64M bit CellularRAM™ compliant products, organized as 4M word by 16 bite; high-speed, CMOS pseudo-static random access memories developed for low-power, portable applications.						
Features	Supports asynchronous and burst operations VCC, VCCQ Voltages: 1.7V–1.95V VCC, 1.7V–1.95V VCCQ Random access time: 70ns Burst mode READ and WRITE access: 4, 8, 16, or 32 words, or continuous burst Burst wrap or sequential Max clock rate: 133 MHz (tCLK = 7.5ns) tACLK: 5.5ns at 133 MHz, 7ns at 104 MHz Low-power features: TCR, PAR, DPD Page mode READ access: Sixteen-word page size Interpage READ access: 70ns, Intrapage READ access: 20ns						
Diagram	N/A						
Package	54VFBGA(6X8X1.0mm), RoHS compliant						
Other Files	<table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td style="width: 10%;"><b>IBIS Model</b></td> <td>N/A</td> </tr> <tr> <td><b>Spice Model</b></td> <td>N/A</td> </tr> <tr> <td><b>Verilog Model</b></td> <td>N/A</td> </tr> </table>	<b>IBIS Model</b>	N/A	<b>Spice Model</b>	N/A	<b>Verilog Model</b>	N/A
<b>IBIS Model</b>	N/A						
<b>Spice Model</b>	N/A						
<b>Verilog Model</b>	N/A						
Development Tools	N/A						
Others	N/A						

Contact us: [PSRAM@winbond.com](mailto:PSRAM@winbond.com)